

FIG. 1

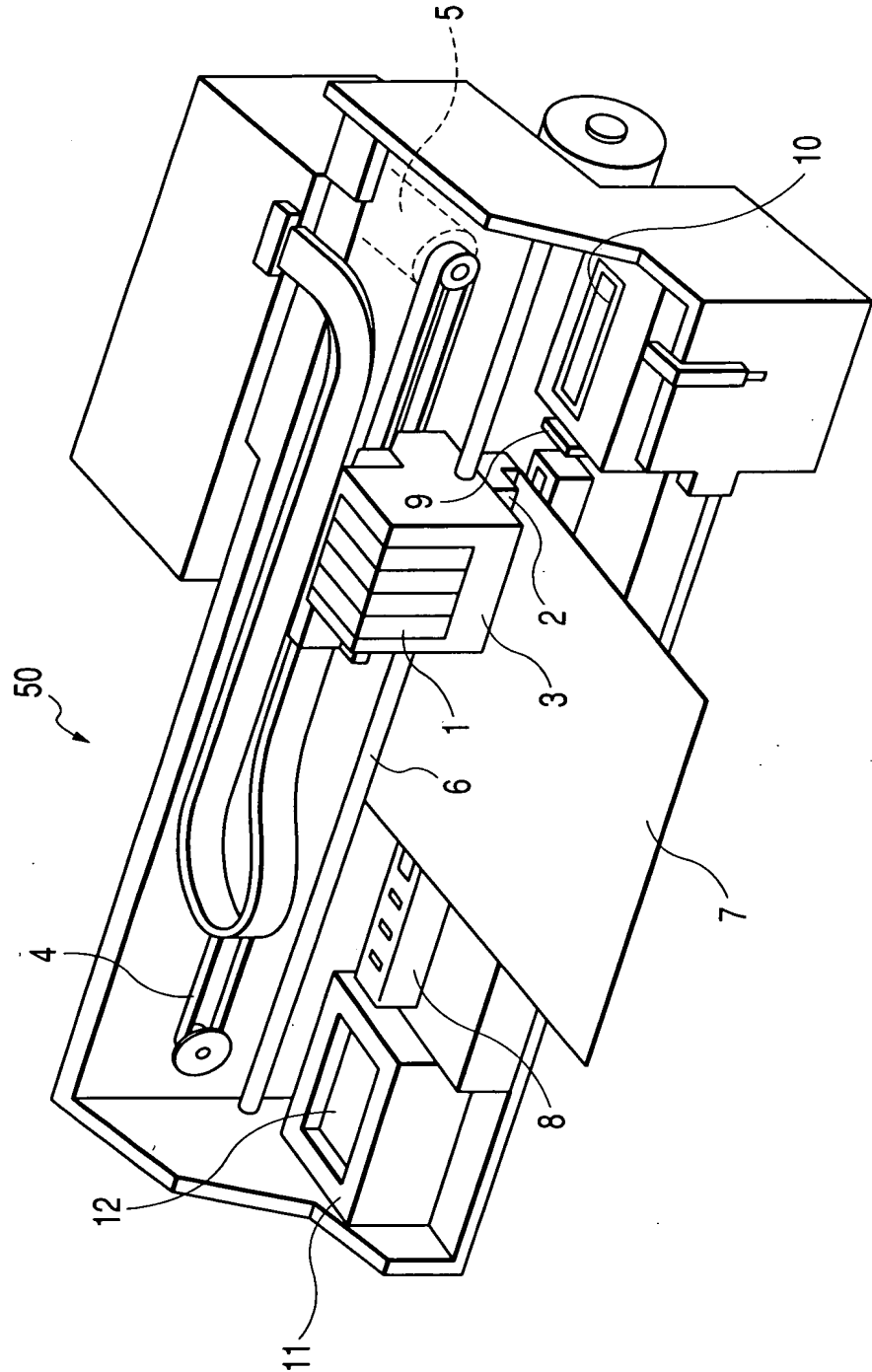


FIG. 2

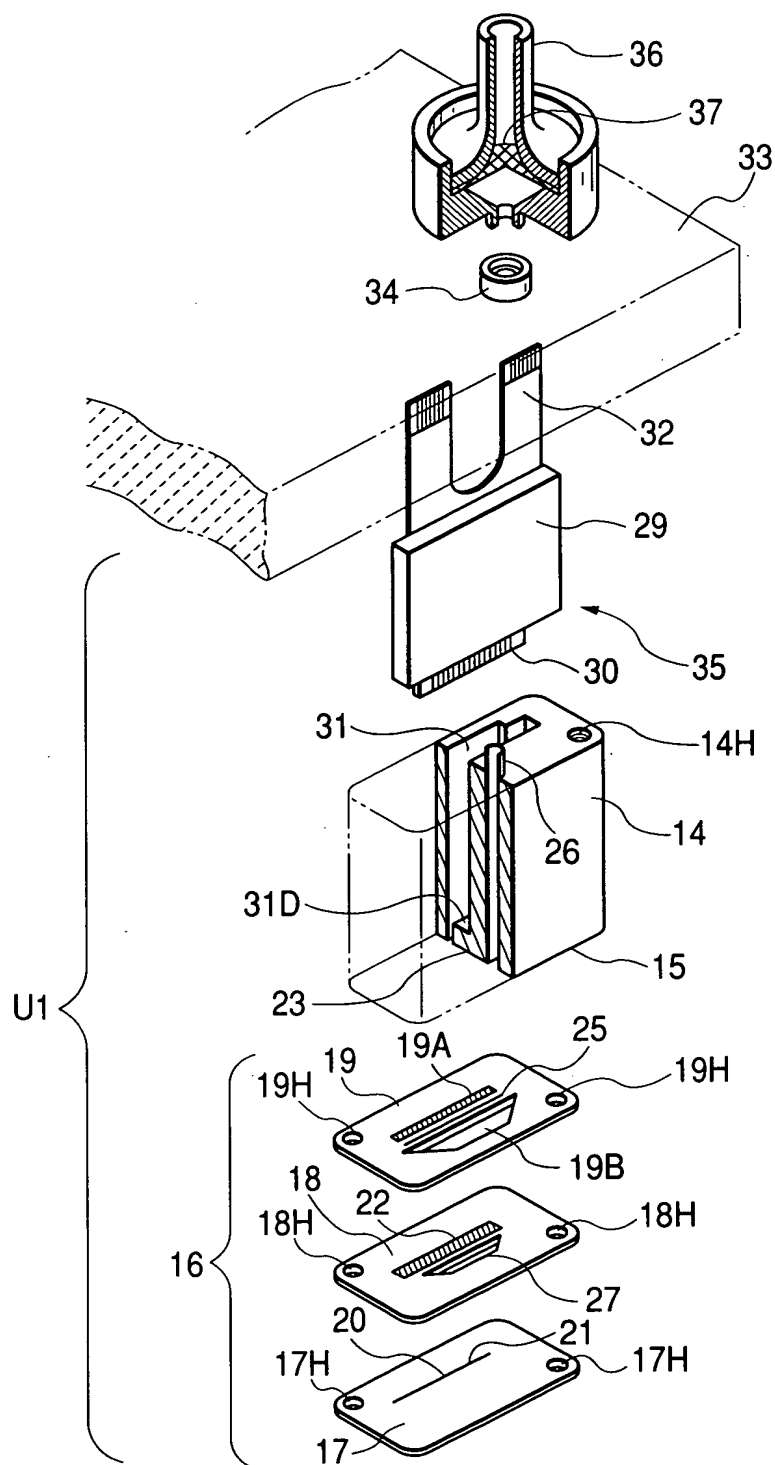


FIG. 3

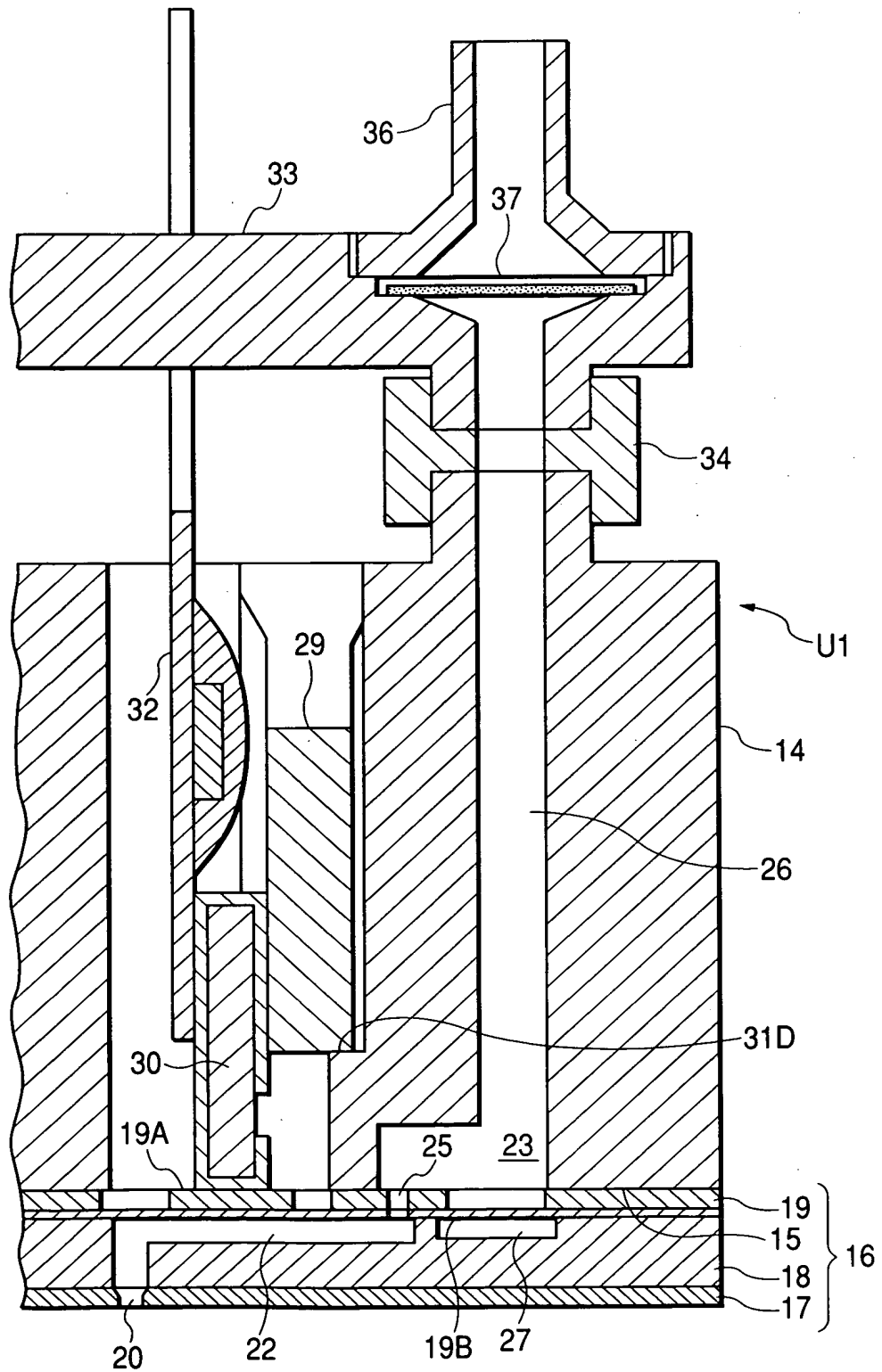


FIG. 4

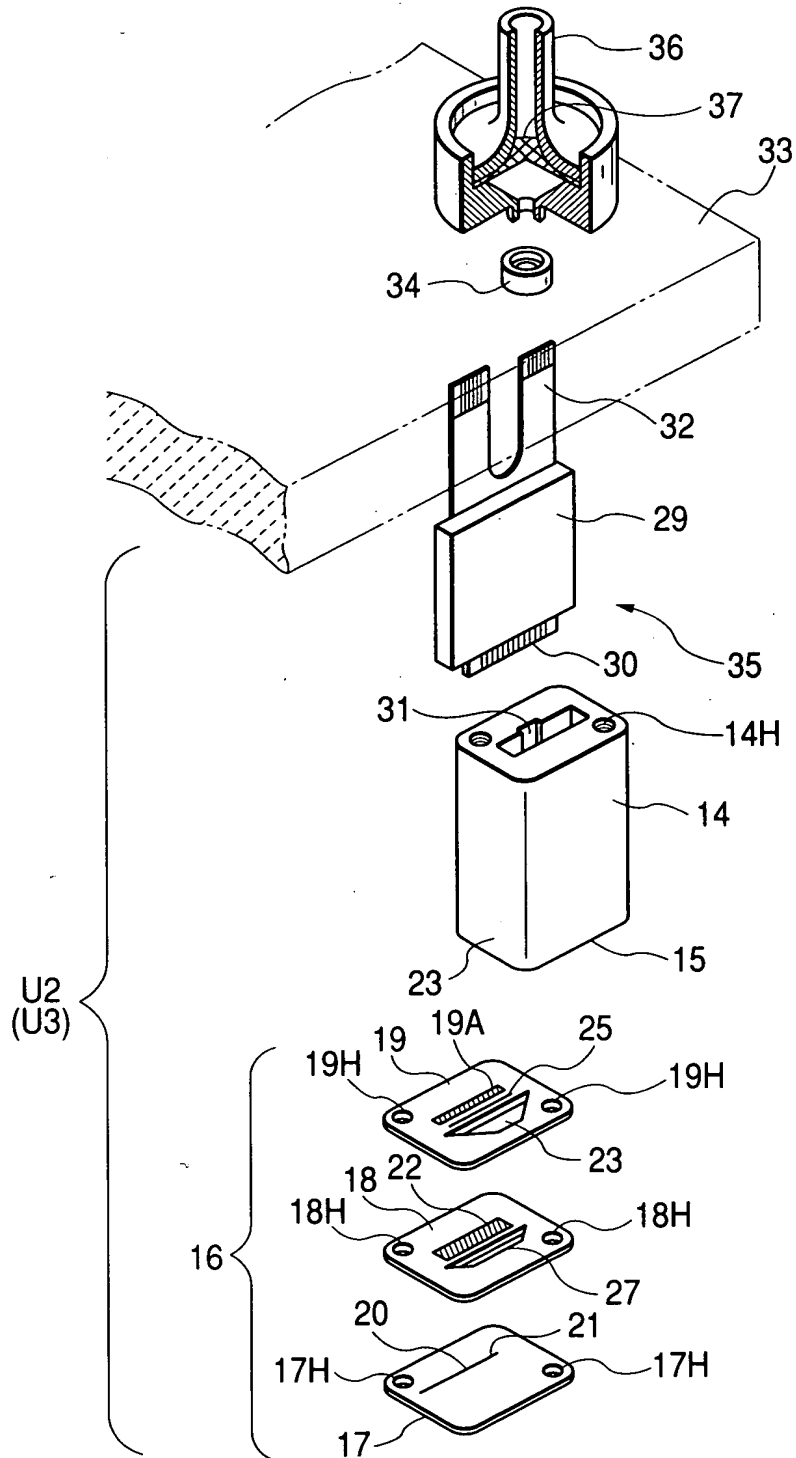


FIG. 5B

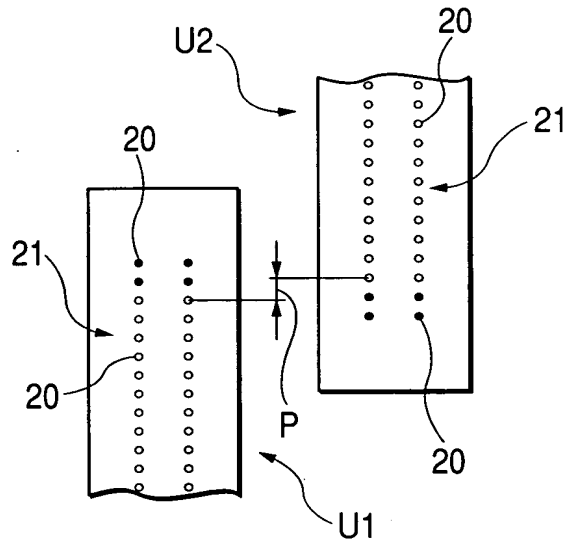


Diagram 3 shows two sheets 39, each having a grid of holes 20. The sheets are separated by a distance $P/2$, and the total distance between the front faces is P . The sheets are labeled 39, 20, and 21.

FIG. 7

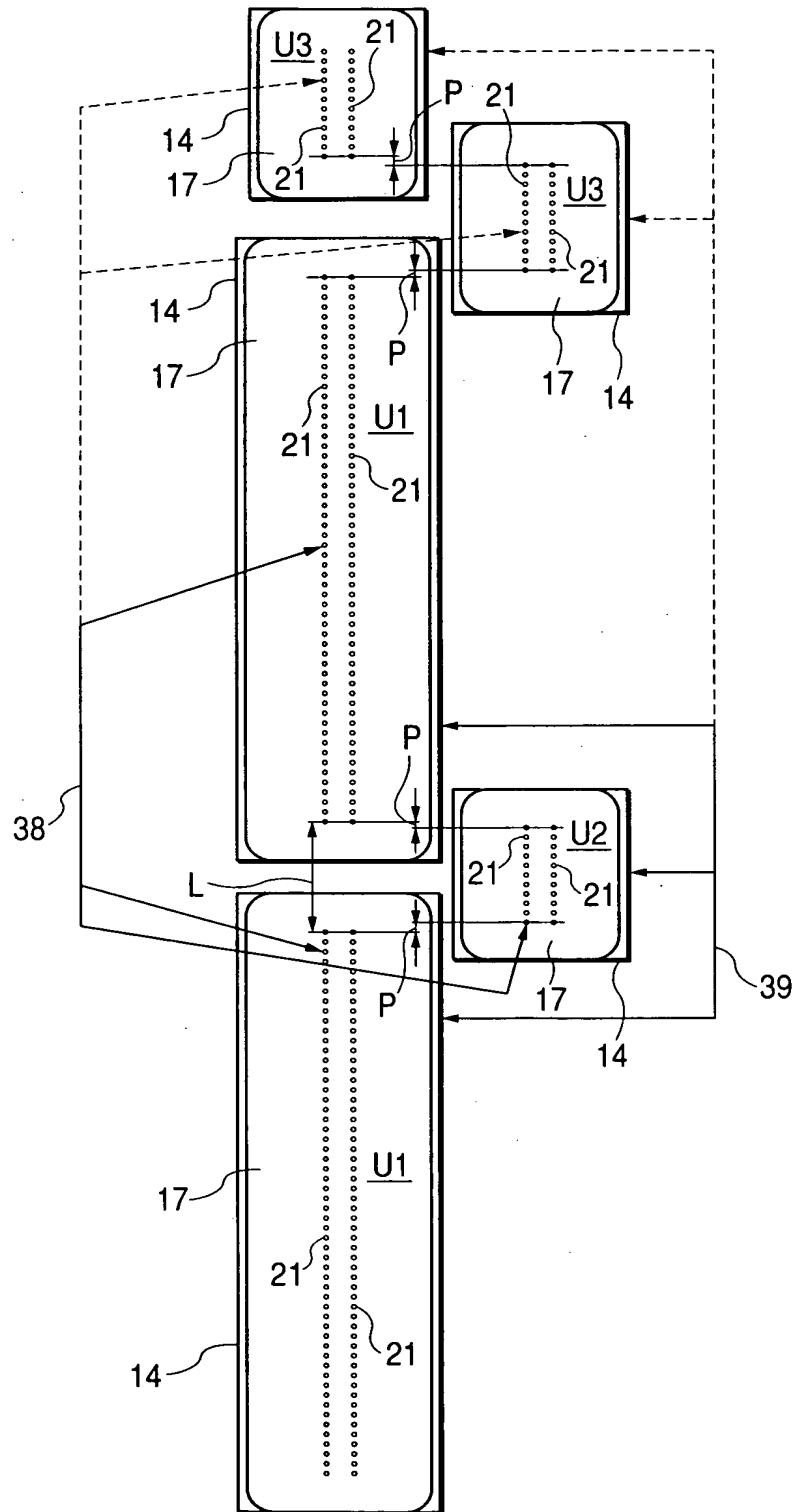


FIG. 8

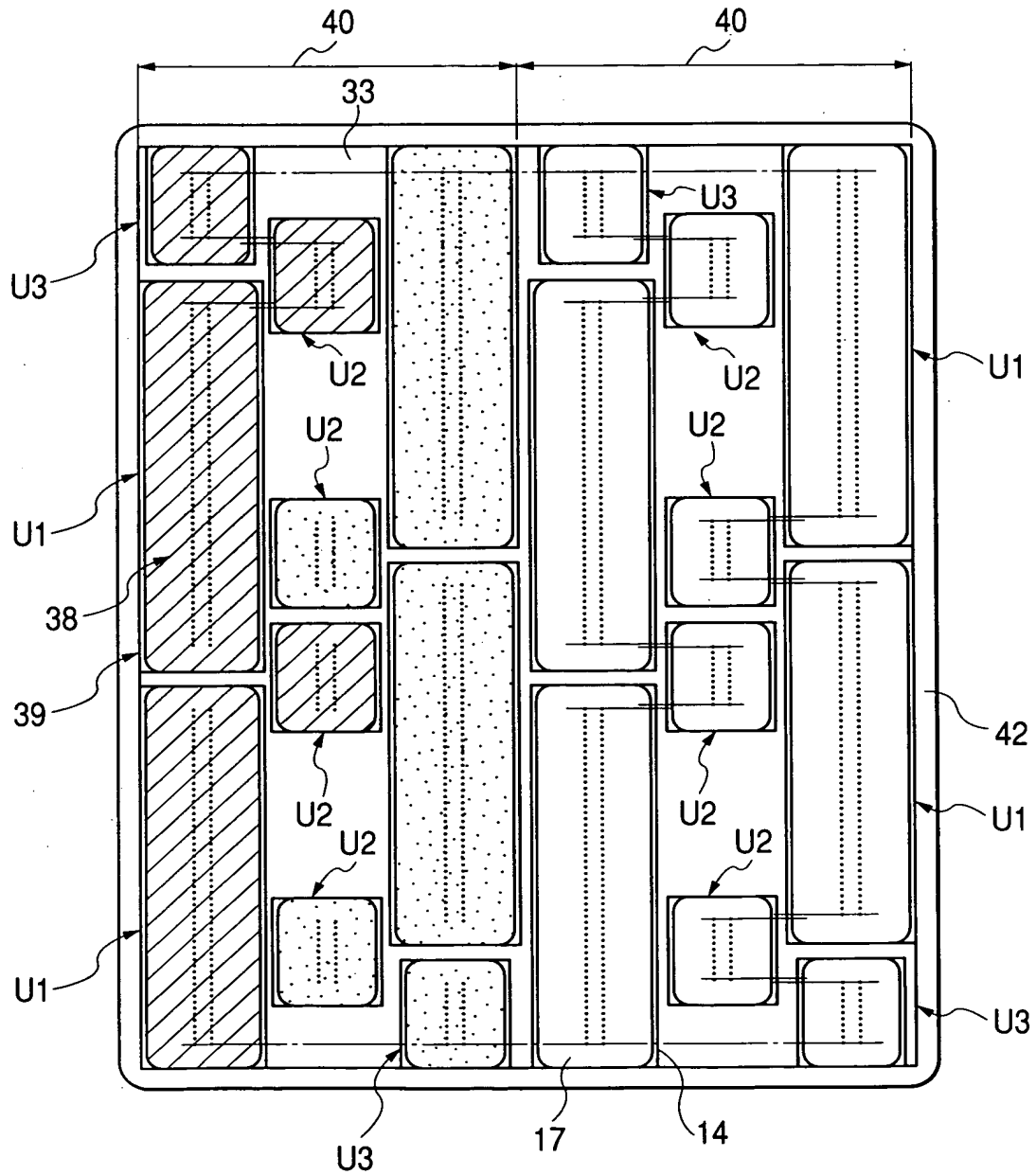
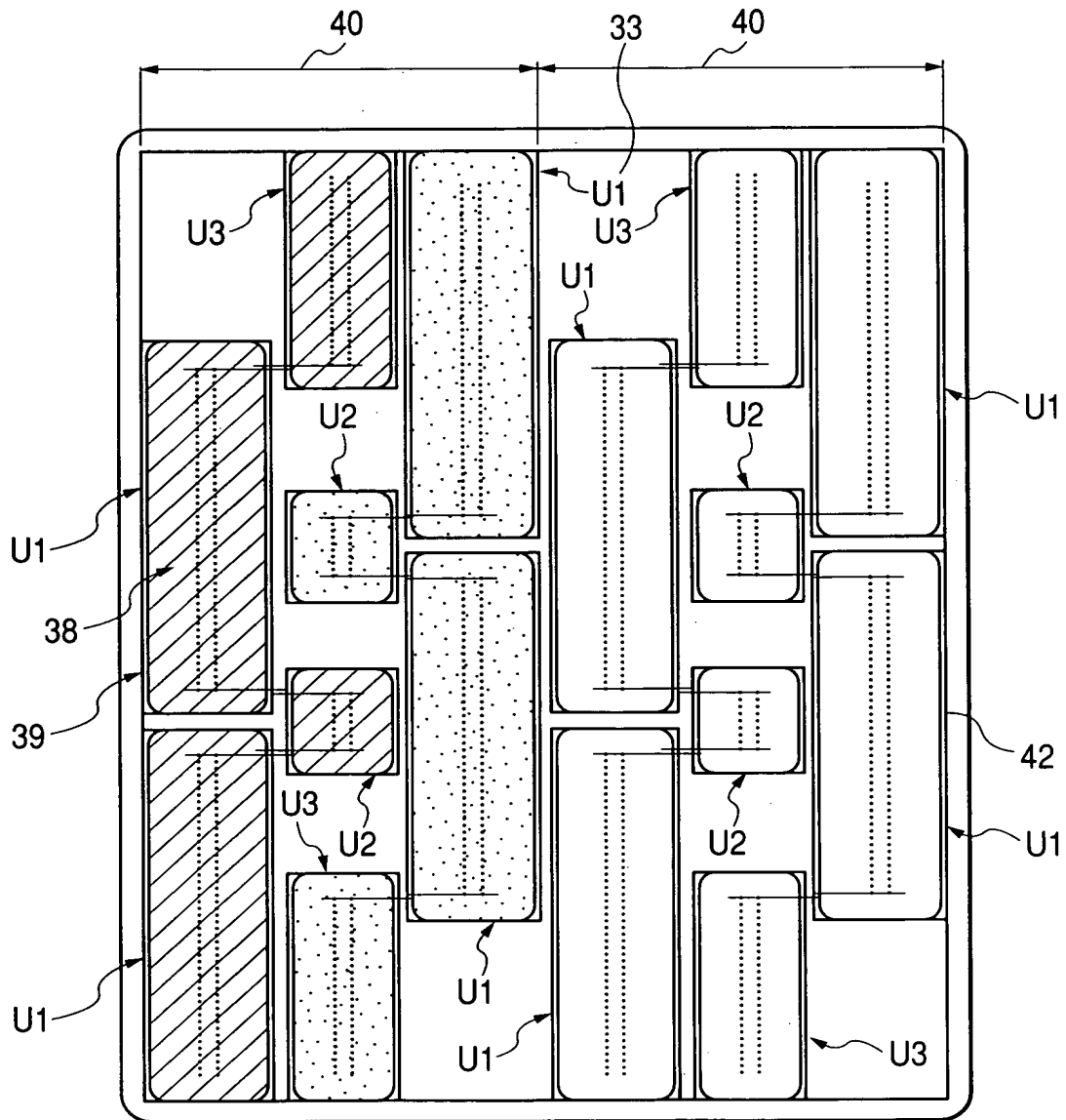


FIG. 9



[illegible]

A cross-sectional view of a semiconductor device. The device features a substrate 33. On the substrate, there are two U-shaped regions, both labeled U1. The left U-shaped region is filled with a material indicated by diagonal hatching. The right U-shaped region is also filled with a material indicated by diagonal hatching. A layer 42 is located on the right side of the device. A layer 43 is located on the top of the left U-shaped region. A layer 45 is located on the top of the right U-shaped region. A layer 16 is located on the top of the device. A layer 45 is also located on the bottom of the device.

FIG. 14

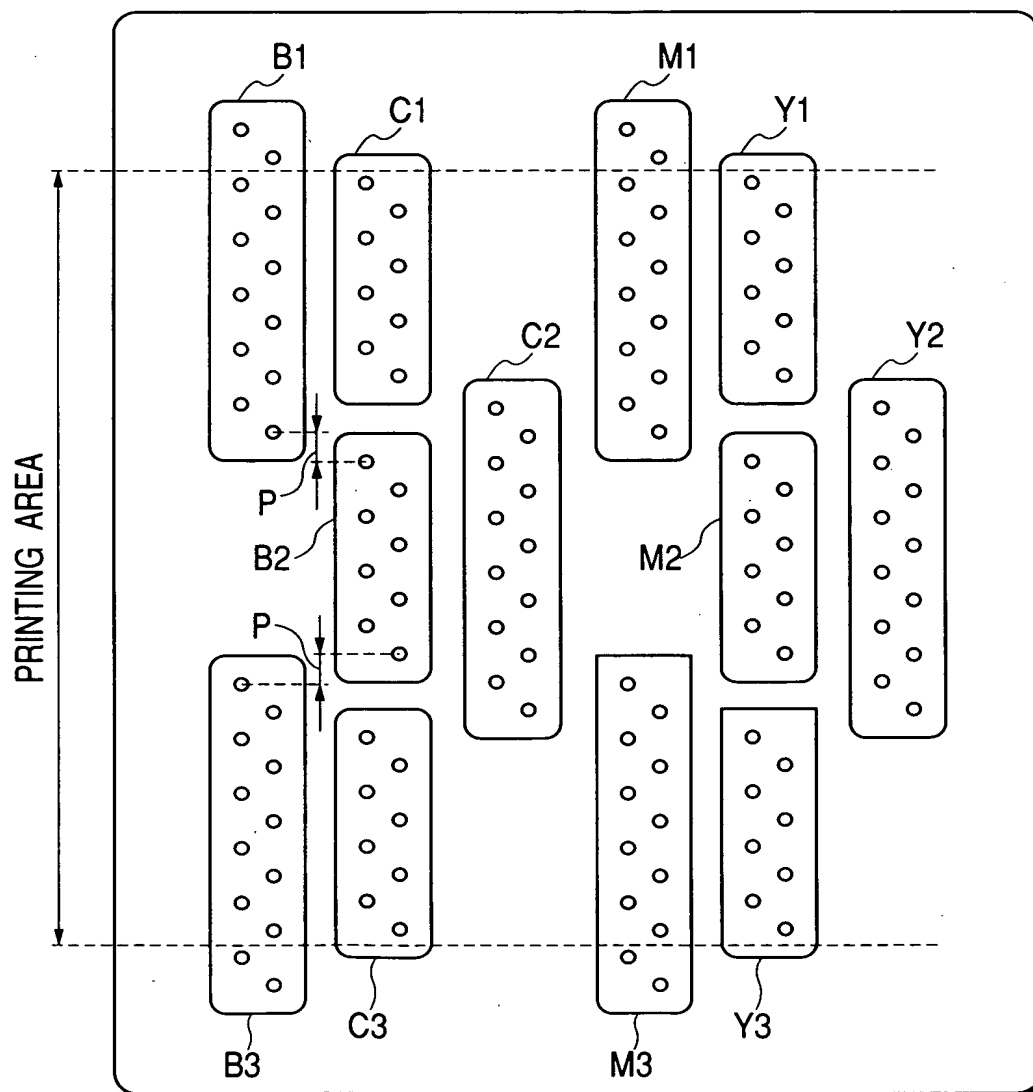


FIG. 15A

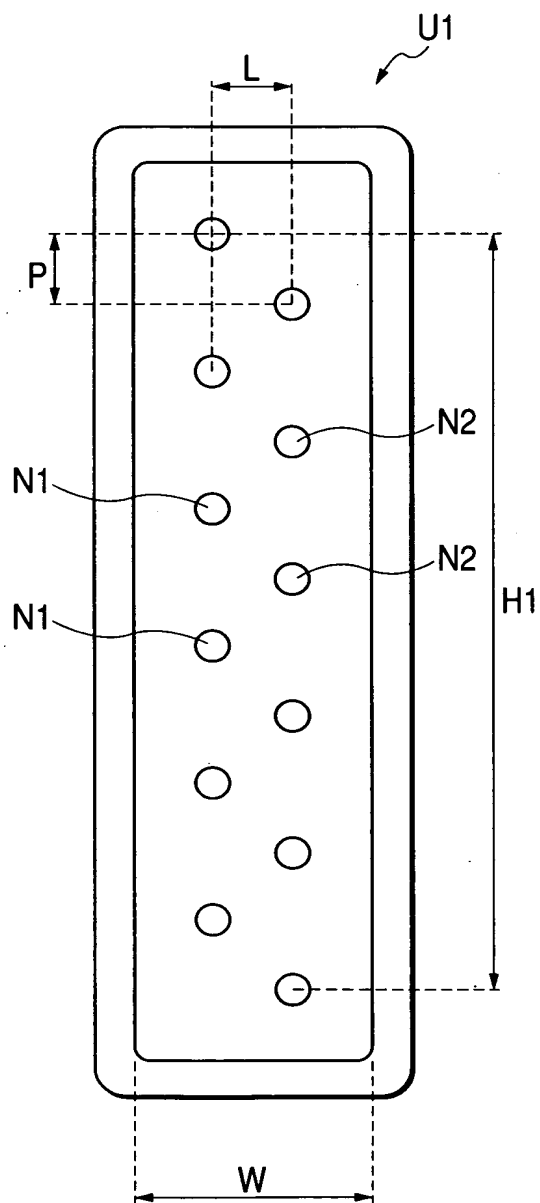


FIG. 15B

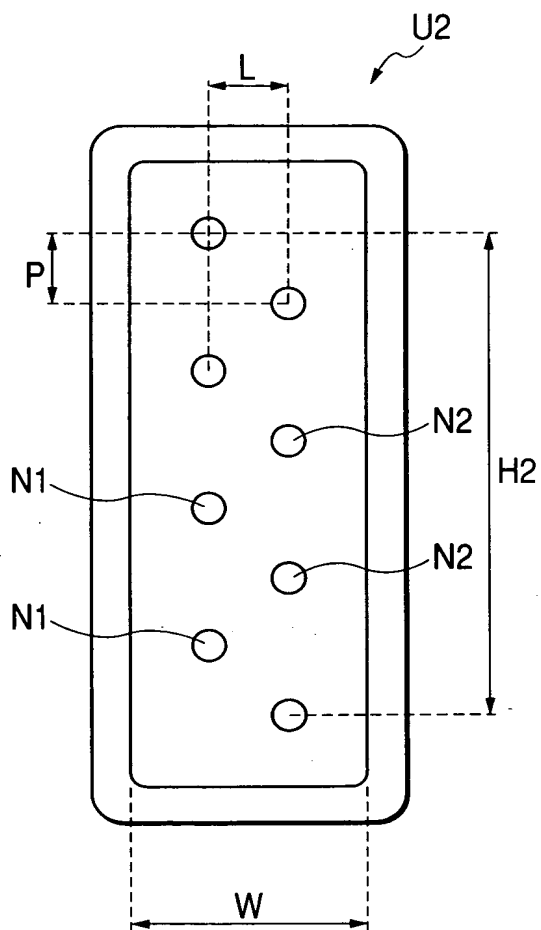


FIG. 16

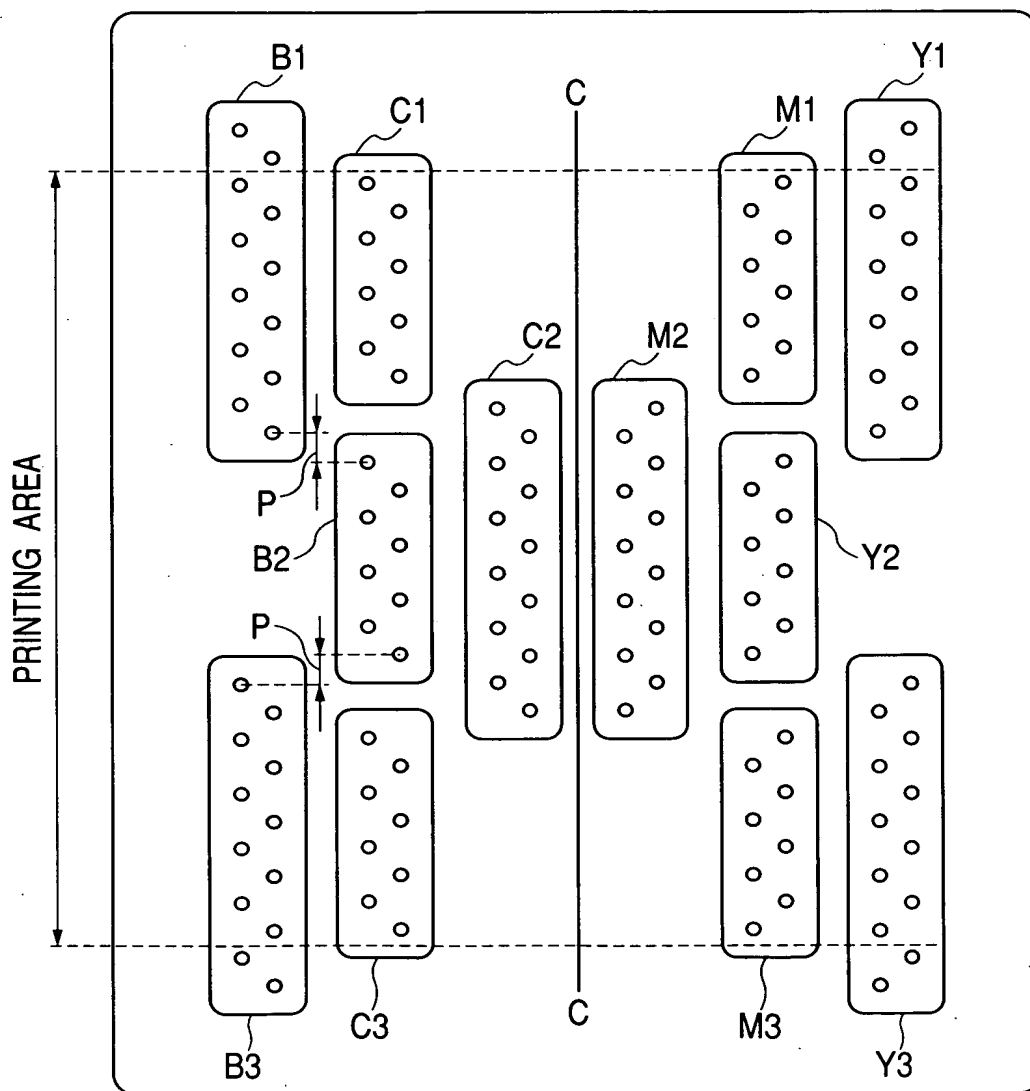


FIG. 17A

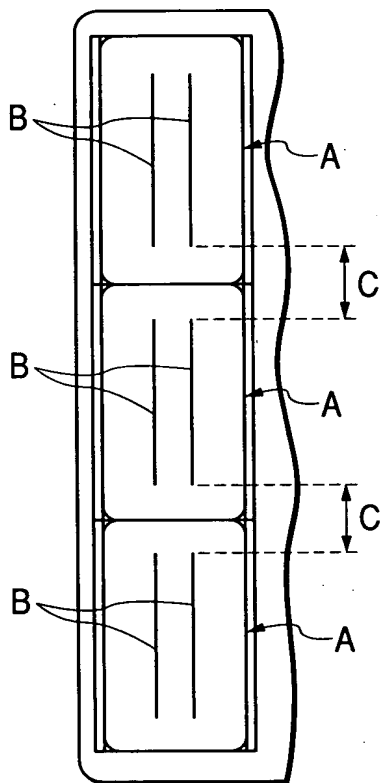


FIG. 17B

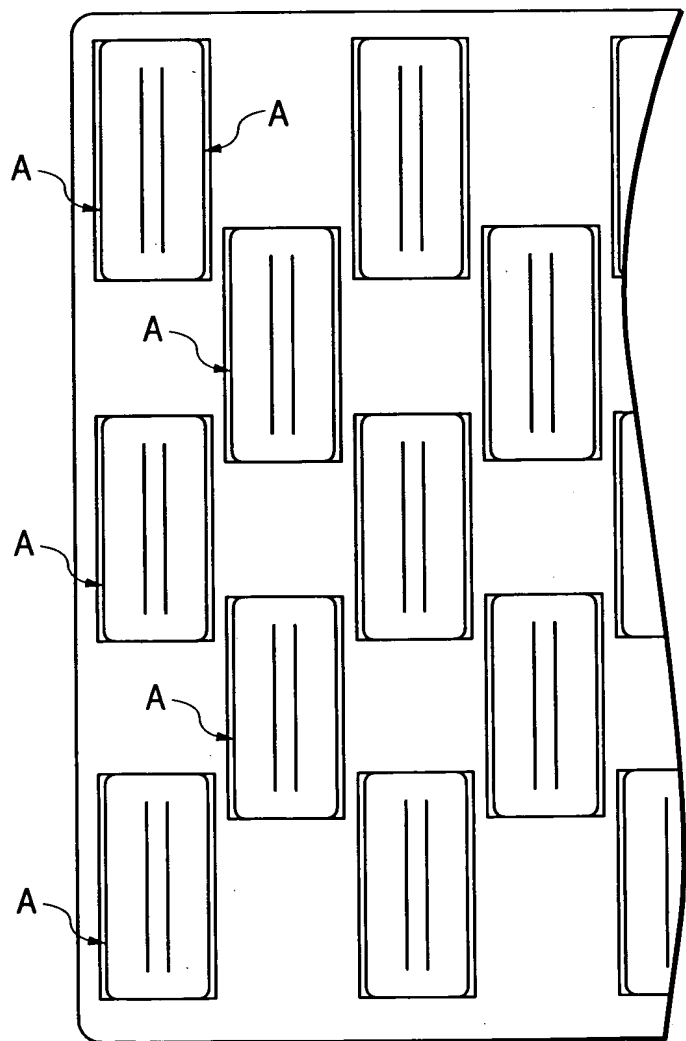


FIG. 18

